

IN THE SPECIFICATOIN

Please replace the paragraph beginning on page 9, line 12 with the following, wherein the amended material is underlined:

The inventor has discovered that a test structure 100 having an area that is about 75% (3/4) of the area of the square-shaped test structure 10 known to the inventor and having a specific geometry, i.e. cross-shaped as shown in FIG. 2, accelerates SIV failure (Stress-Induced Voiding failure). Cross-shaped test structure 100 has a thickness of preferably from about 5000 to 10,000 Å and more preferably about 5000 Å. The cross-shaped test structure 100 is embedded and exposed within a dielectric layer formed over the silicon wafer. In a preferred embodiment of the invention, the test structure 100 comprises a first member 190 having a roughly rectangular shape with a first width dimension W1 and a first length dimension L1 that is greater than the first width dimension W1, and a second member 192 having a roughly rectangular shape having a second width dimension W2 and a second length dimension L2 that is greater than the second width dimension W2. The second member 192 is combined with the first member 190 to form a roughly symmetrical cross-shaped test structure 100. Preferably, W1 is larger than (L2-W1)/2, W1 is larger than (L1-W2)/2, W2 is larger than (L2-W1)/2, and/ or W2 is larger than (L1-W2)/2.